



SFT1445

N-Channel Power MOSFET 100V, 17A, 111mΩ, Single TP/TP-FA

ON Semiconductor®

<http://onsemi.com>

Features

- ON-resistance $R_{DS(on)} = 85\text{m}\Omega$ (typ.)
- Input Capacitance $C_{iss} = 1030\text{pF}$ (typ.)
- 4V drive
- Halogen free compliance
- Protection diode in

Specifications

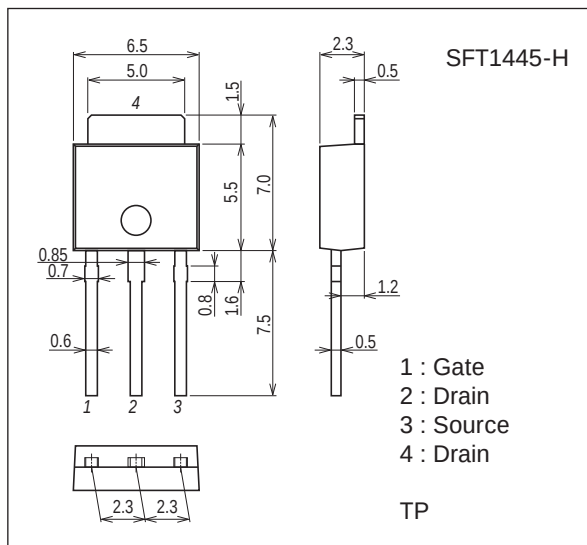
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		100	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		17	A
Drain Current (PW≤10μs)	I_{DP}	PW≤10μs, duty cycle≤1%	68	A
Allowable Power Dissipation	P_D		1.0	W
		$T_c = 25^\circ\text{C}$	35	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

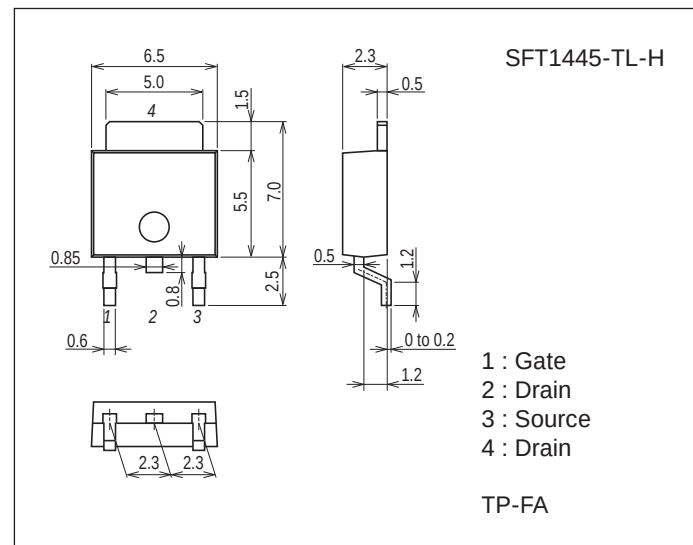
Package Dimensions unit : mm (typ)

7518-004



Package Dimensions unit : mm (typ)

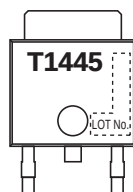
7003-004



Product & Package Information

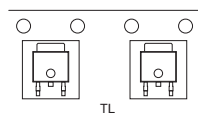
- Package : TP
- JEITA, JEDEC : SC-64, TO-251
- Minimum Packing Quantity : 500 pcs./bag

Marking (TP, TP-FA)

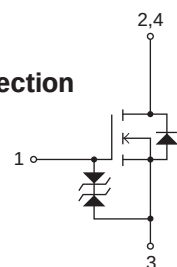


- Package : TP-FA
- JEITA, JEDEC : SC-63, TO-252
- Minimum Packing Quantity : 700 pcs./reel

Packing Type (TP-FA) : TL



Electrical Connection

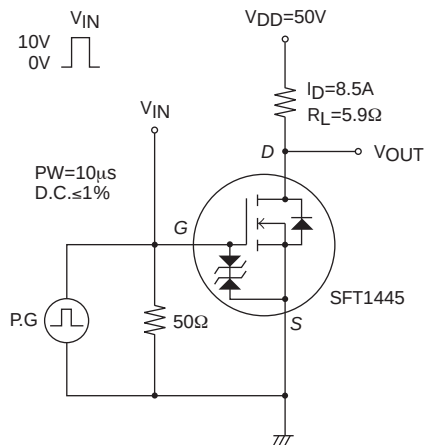


SFT1445

Electrical Characteristics at Ta=25°C

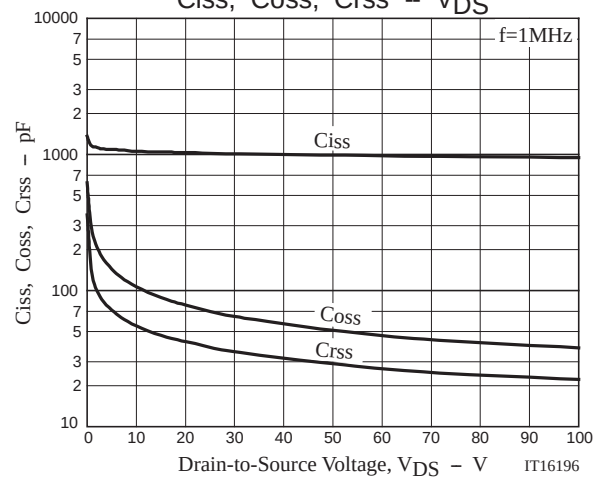
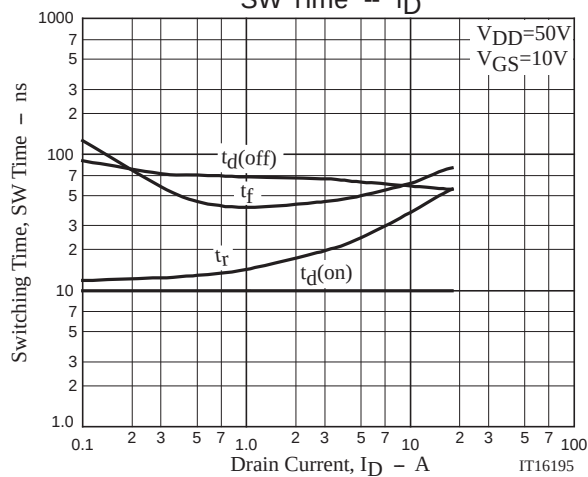
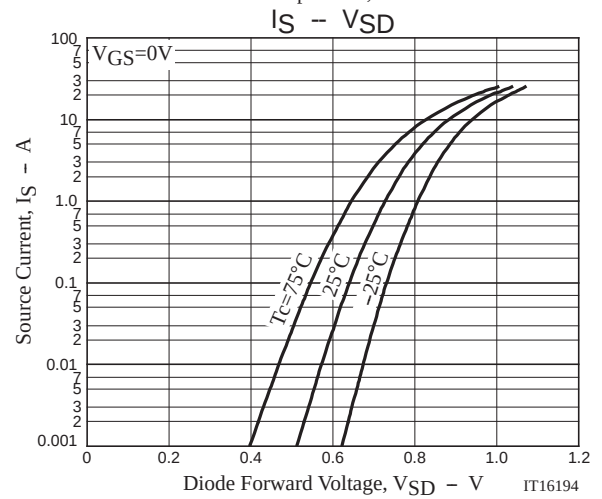
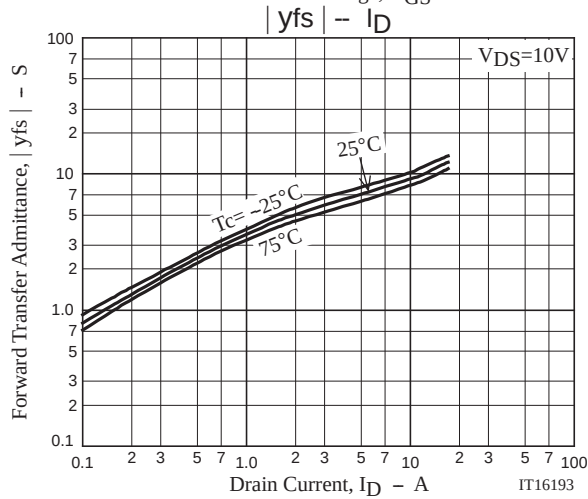
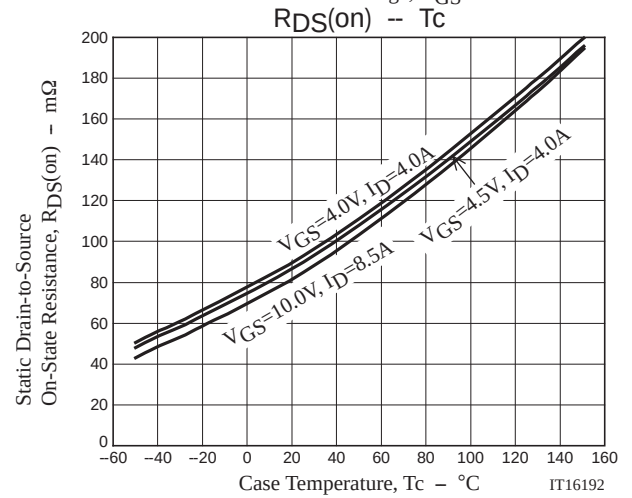
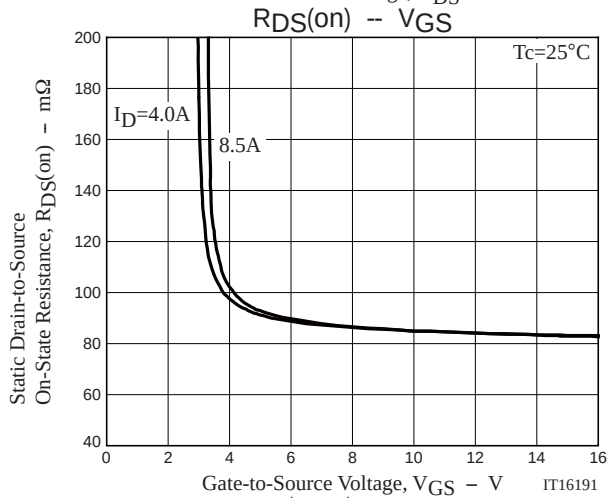
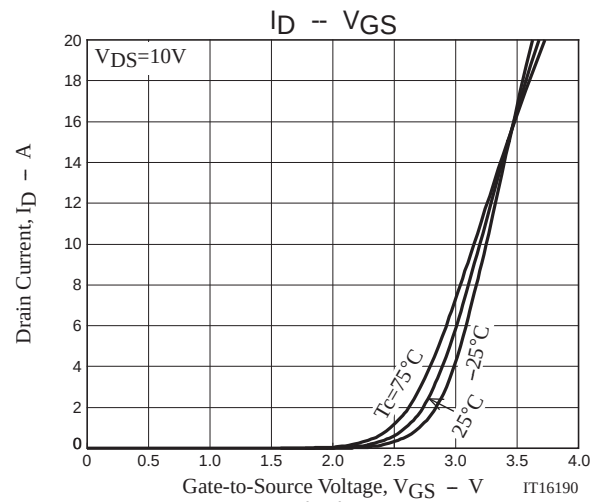
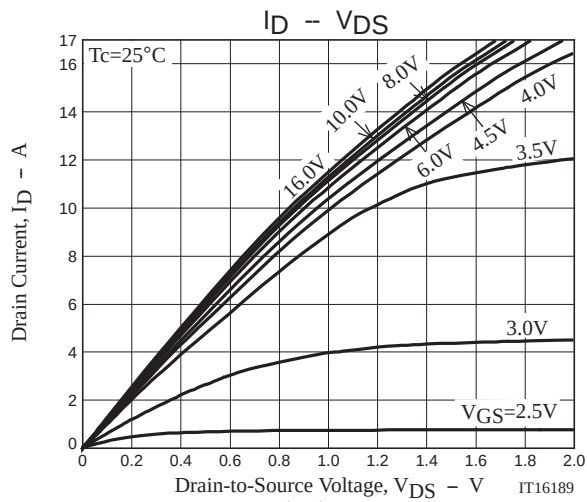
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	100			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=8.5A$		8.9		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=8.5A, V_{GS}=10V$		85	111	$m\Omega$
	$R_{DS(on)2}$	$I_D=4A, V_{GS}=4.5V$		90	126	$m\Omega$
	$R_{DS(on)3}$	$I_D=4A, V_{GS}=4V$		93	130	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		1030		pF
Output Capacitance	C_{oss}			78		pF
Reverse Transfer Capacitance	C_{rss}			42		pF
Turn-ON Delay Time	$t_d(on)$			10		ns
Rise Time	t_r	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	$t_d(off)$			60		ns
Fall Time	t_f			60		ns
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=10V, I_D=17A$		19		nC
Gate-to-Source Charge	Q_{gs}			3.6		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			3.8		nC
Diode Forward Voltage	V_{SD}	$I_S=17A, V_{GS}=0V$		0.96	1.2	V

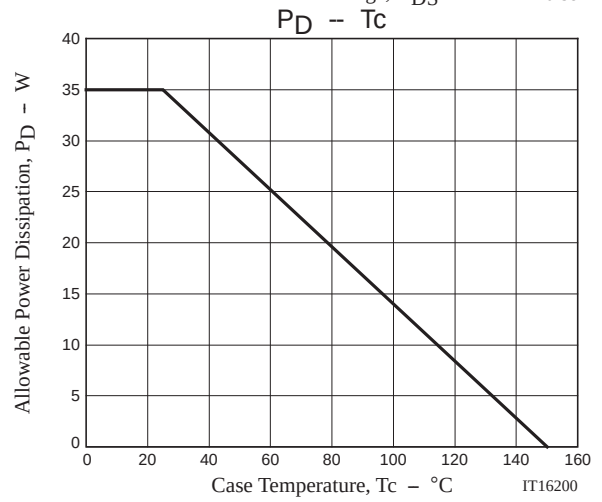
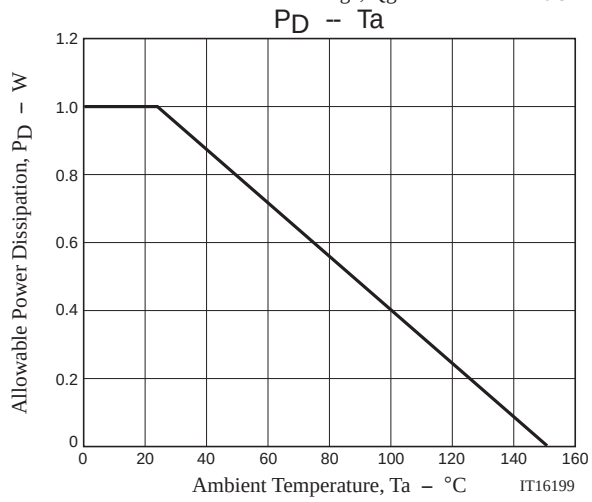
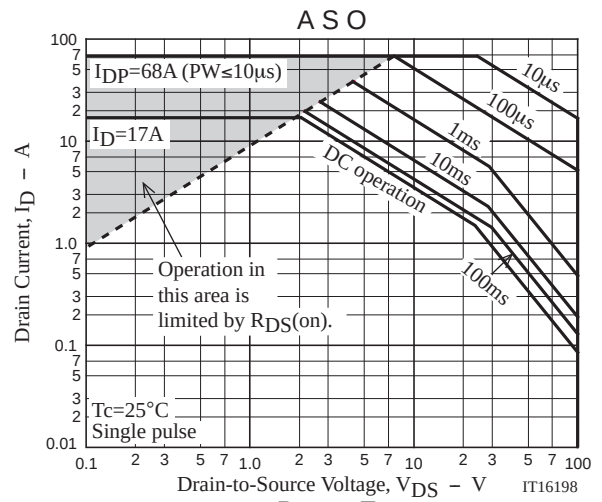
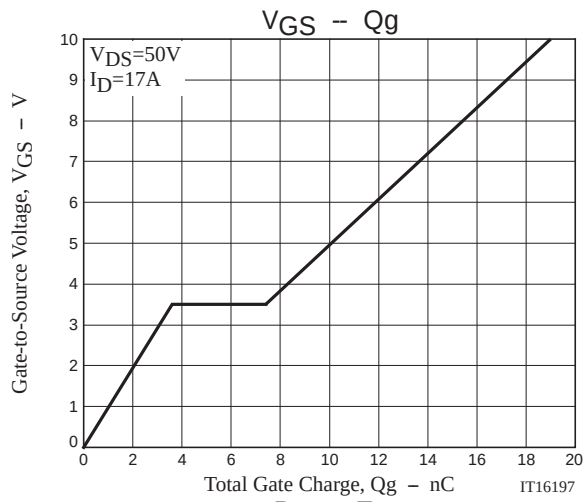
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
SFT1445-H	TP	500pcs./bag	Pb Free and Halogen Free
SFT1445-TL-H	TP-FA	700pcs./reel	





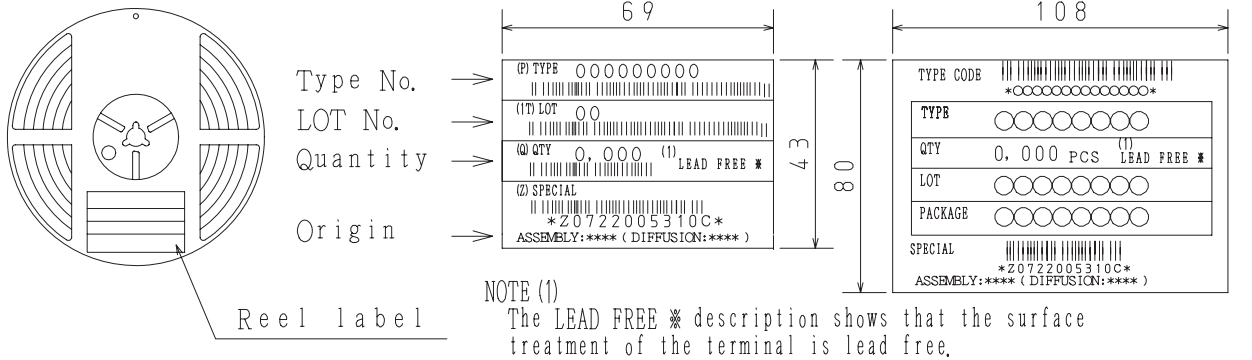
Taping Specification

SFT1445-TL-H

Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
TP-FA	TP	700	2, 100	12, 600	3 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

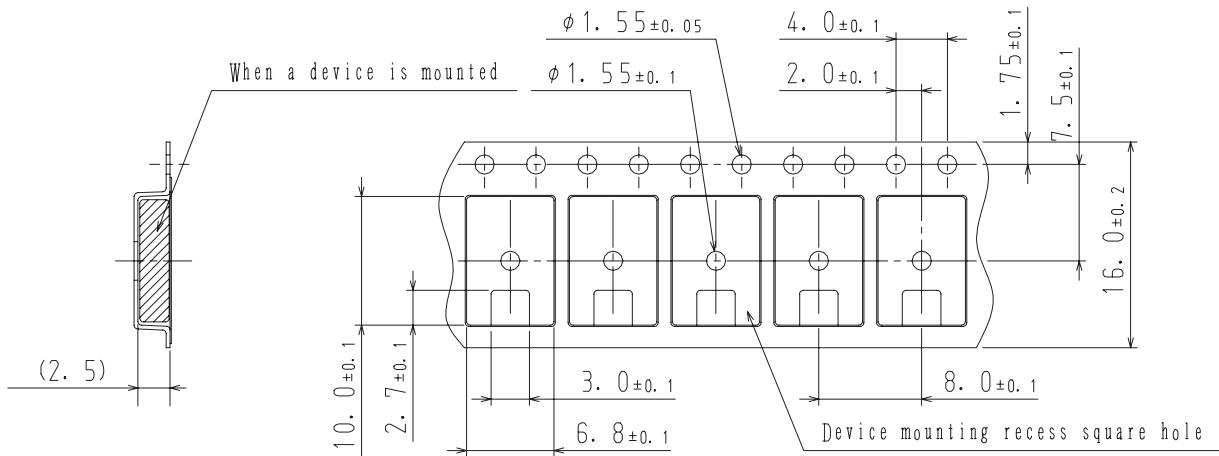
Packing method



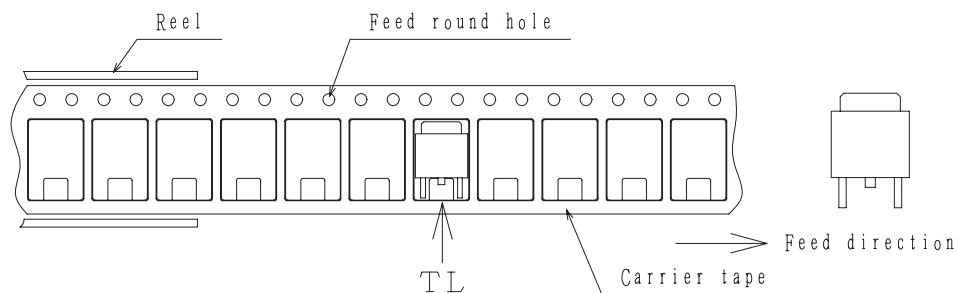
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

Taping configuration

1. Carrier tape size (unit:mm)

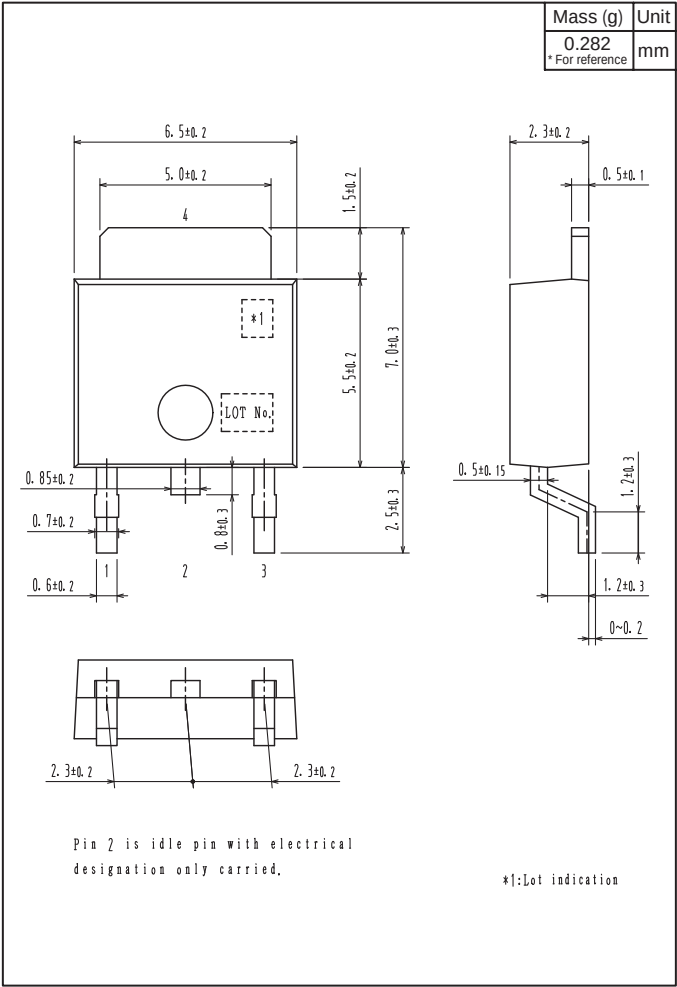


2. Device placement direction

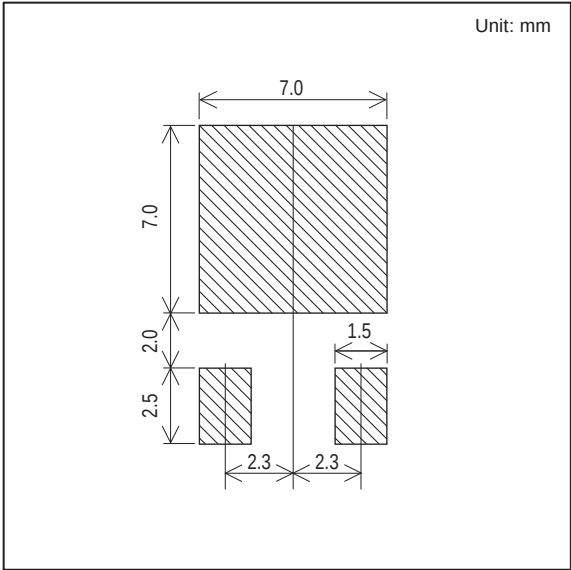


Those with one electrode terminal on the feed hole side.....TL

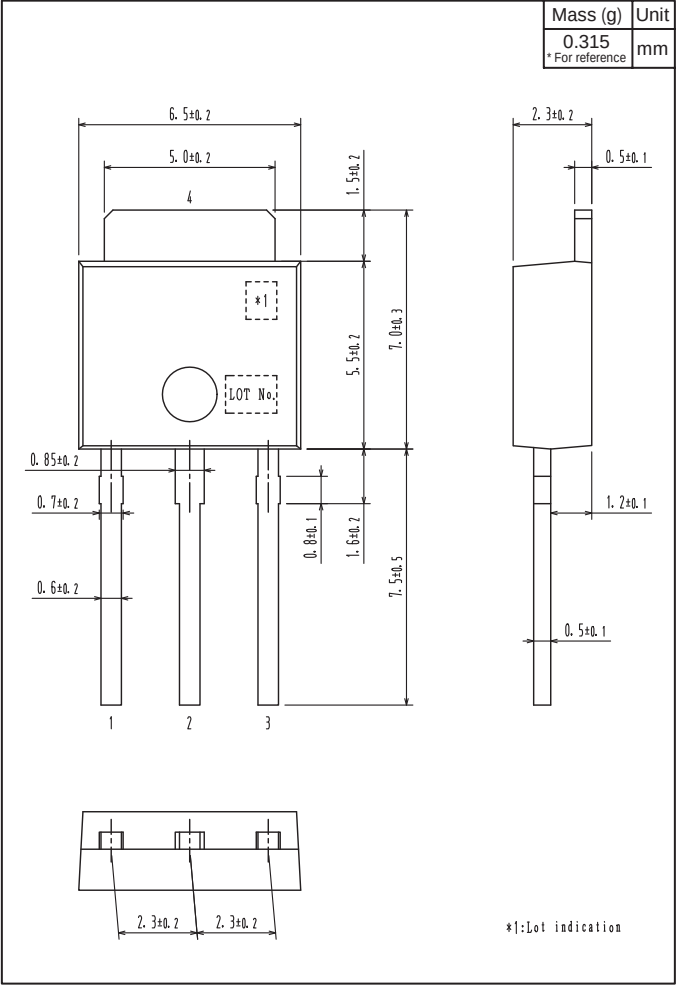
Outline Drawing
SFT1445-TL-H



Land Pattern Example



Outline Drawing
SFT1445-H



Note on usage : Since the SFT1445 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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